

Method for Transistor Gate Dielectric Layer with Uniform Nitrogen Concentration

5 ABSTRACT OF THE INVENTION

The instant invention describes a method for forming a dielectric film with a uniform concentration of nitrogen. The films are formed by first incorporating nitrogen into a dielectric film using RPNO. The films are then annealed in
10 N₂O which redistributes the incorporated species to produce a uniform nitrogen concentration.

40360 4402360